Supplementary Materials for

Nanostripe-confined catalyst formation for uniform growth of ultrathin silicon nanowires

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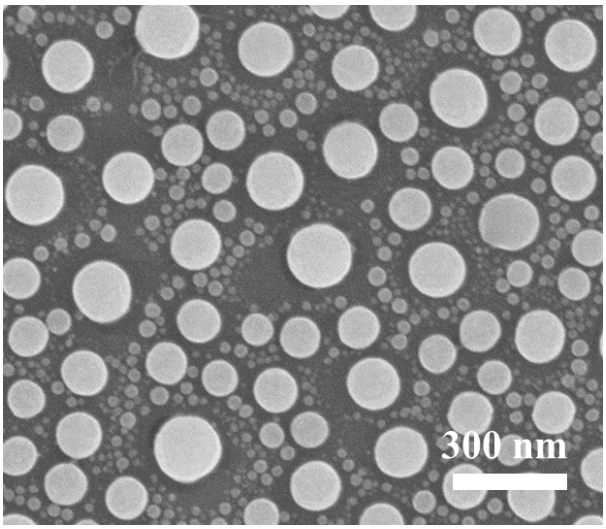

Figure S1. The SEM image of the catalyst droplet dispersion on planar surface after H_2 plasma treatment. The average separation can be estimated from the density by $d_s = n_{In}^{-1/2} \sim 244\ nm$.

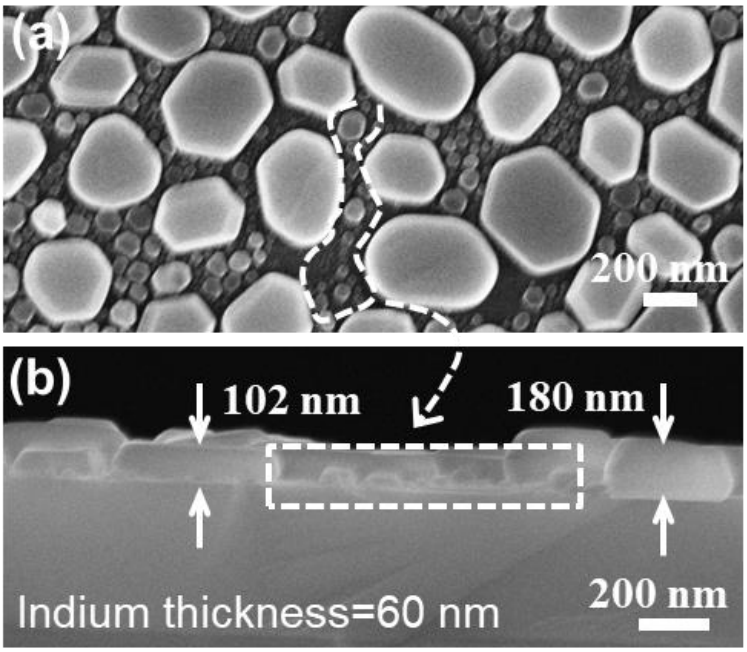

Figure S2. (a) The SEM image of In grains deposited on planar surface. (b) The cross-section view of the deposited In grains. The small grains only exist in the spare regions among the large grains, with a much lower height than their larger neighbors.

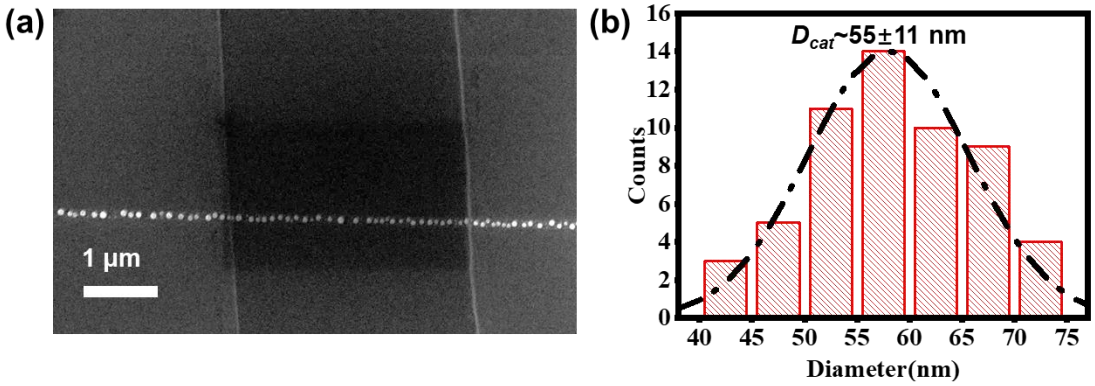

Figure S3. (a) SEM image of In droplets formed on 70 nm stripe after H_2 plasma treatment. (b) The diameter statistics of the as-received In droplets, with D_{cat} of 55 nm±11 nm.

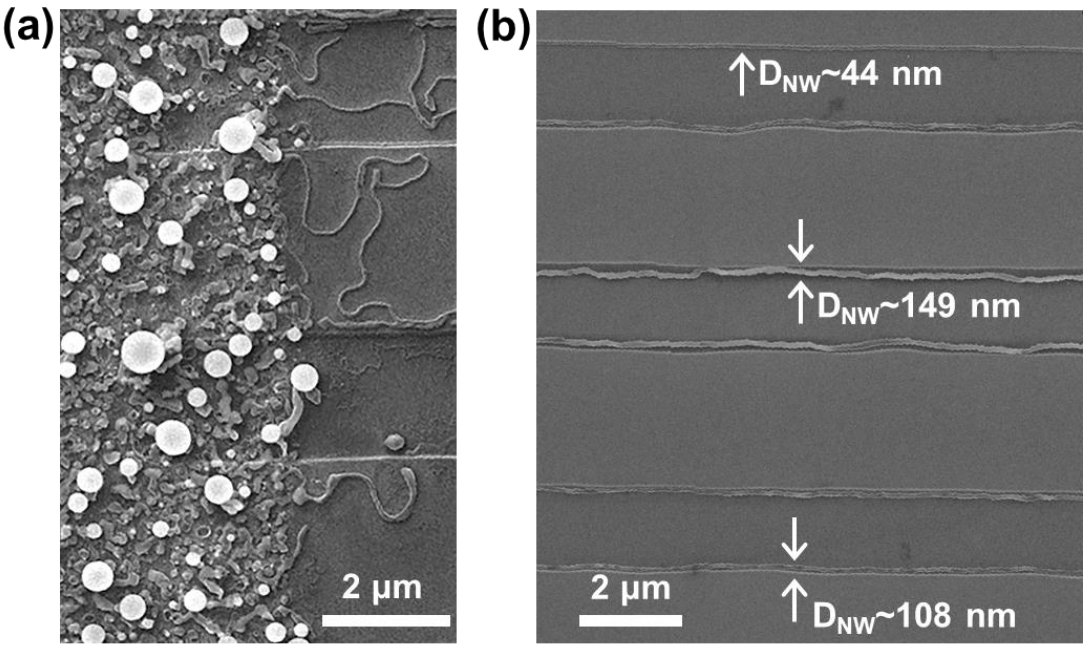

Figure S4. The guided growth of SiNW arrays via the IPSLS mode by using catalysts formed within wide stripe (> 2μm), which shows the large diameter variation of formed catalysts (a) and the as-grown SiNW (b).